CLAIMS

1. An Al wiring material containing one or more of Pd and Pt so as to satisfy

$3 \leq x1a \leq 90$ or $10 \leq x1b \leq 250$, and

$3 \leq (x1a + x1b) \leq 300$,

where x1a and x1b are respectively a content of Pd [mass ppm] and a content of Pt [mass ppm],

with the balance comprising Al, and

an average crystal grain diameter on a cross-section perpendicular to a longitudinal direction of the Al wiring material is 3 to 35 μm,

wherein, on the cross-section perpendicular to the longitudinal direction of the Al wiring material, an orientation ratio of a crystal orientation <111> angled at 15 degrees or less to the longitudinal direction of the Al wiring material is equal to or higher than 0.5% and equal to or lower than 35%.

2. The Al wiring material according to claim 1, wherein a tensile strength is equal to or larger than 25 MPa and equal to or smaller than 95 MPa.

3. The Al wiring material according to claim 1 or 2, further containing one or more of Mg, Mn, and Cu so as to satisfy

$200 \leq x2 \leq 6000$

where x2 is a total content thereof [mass ppm].

4. The Al wiring material according to any one of claims 1 to 3, further containing one or more of Fe, Si, and Ni so as to satisfy

$10 \leq x3 \leq 2000$

where x3 is a total content thereof [weight ppm].

5. The Al wiring material according to any one of claims 1 to 4, wherein a content of Al is equal to or larger than 98% by mass.

6. The Al wiring material according to any one of claims 1 to 5, wherein a balance of the Al bonding wire comprises Al and inevitable impurities.

7. A semiconductor device comprising the Al wiring material according to any one of claims 1 to 6.